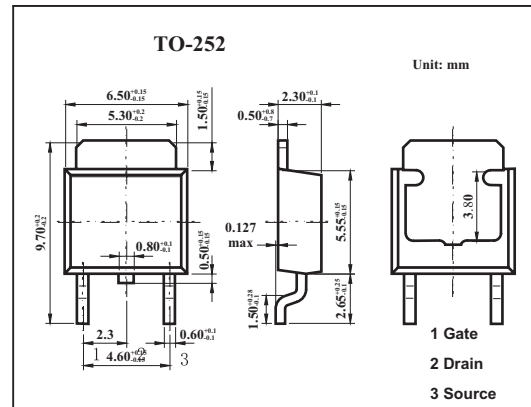


## MOS Field Effect Transistor

### 2SK3635

#### ■ Features

- High voltage:  $V_{bss} = 200\text{ V}$
- Gate voltage rating:  $\pm 30\text{ V}$
- Low on-state resistance  
 $R_{DS(on)} = 0.43\ \Omega\ \text{MAX.}$  ( $V_{GS} = 10\text{ V}$ ,  $I_D = 4.0\text{ A}$ )
- Low  $C_{iss}$ :  $C_{iss} = 390\text{ pF TYP.}$
- Built-in gate protection diode



#### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Drain to source voltage	$V_{bss}$	200	V
Gate to source voltage	$V_{GSS}$	$\pm 30$	V
Drain current	$I_D$	$\pm 8.0$	A
	$I_{DP}^*$	$\pm 24$	A
Power dissipation	$P_D$	$T_C=25^\circ\text{C}$	24
		$T_A=25^\circ\text{C}$	1.0
Channel temperature	$T_{ch}$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

\*  $PW \leq 10\ \mu\text{s}$ , Duty Cycle  $\leq 1\%$

#### ■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit	
Drain cut-off current	$I_{DSS}$	$V_{DS}=200\text{V}, V_{GS}=0$			10	$\mu\text{A}$	
Gate leakage current	$I_{GSS}$	$V_{GS}=\pm 30\text{V}, V_{DS}=0$			$\pm 10$	$\mu\text{A}$	
Gate cut off voltage	$V_{GS(off)}$	$V_{DS}=10\text{V}, I_D=1\text{mA}$	2.5	3.5	4.5	V	
Forward transfer admittance	$ Y_{fs} $	$V_{DS}=10\text{V}, I_D=4.0\text{A}$	3.	5		S	
Drain to source on-state resistance	$R_{DS(on)}$	$V_{GS}=10\text{V}, I_D=4.0\text{A}$		0.34	0.43	$\Omega$	
Input capacitance	$C_{iss}$	$V_{DS}=10\text{V}, V_{GS}=0, f=1\text{MHz}$		390		pF	
Output capacitance	$C_{oss}$				95		pF
Reverse transfer capacitance	$C_{rss}$				45		pF
Turn-on delay time	$t_{on}$	$I_D=4.0\text{A}, V_{GS(on)}=10\text{V}, R_G=0\ \Omega, V_{DD}=100\text{V}$		5		ns	
Rise time	$t_r$				7		ns
Turn-off delay time	$t_{off}$				19		ns
Fall time	$t_f$				6		ns
Total Gate Charge	$Q_G$		$V_{DD} = 160\text{V}$		12		nC
Gate to Source Charge	$Q_{GS}$	$V_{GS} = 10\text{ V}$		2		nC	
Gate to Drain Charge	$Q_{GD}$	$I_D = 8.0\text{A}$		6		nC	